Description

The SI2309 is the high cell density trenched P-ch MOSFETs, which provides excellent RDSON and efficiency for most of the small power switching and load switch applications.

The SI2309 meet the RoHS and Green Productrequirement with full function reliability approved.



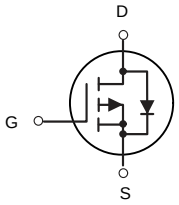
SOT-23

General Features

V_{DS} = -60V,I_D = -2A

$R_{DS(ON)}$ <200mΩ @ V_{GS}=-10V

$R_{DS(ON)}$ <300mΩ @ V_{GS}=-4.5V



P-Channel MOSFET

Application

Load switch

PWM application

Ordering Information

Product ID	Pack	Brand	Qty(PCS)
SI2309	SOT-23	HXY MOSFET	3000

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Limit	Unit
V_{DS}	Drain-Source Voltage	-60	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Drain Current-Continuous	-2	A
I_{DM}	Drain Current-Pulsed (Note 1)	-5.2	A
P_D	Maximum Power Dissipation	1	W
T_J,T_{STG}	Operating Junction and Storage Temperature Range	-55 To 150	℃
$R_{\theta JA}$	Thermal Resistance,Junction-to-Ambient (Note 2)	83.3	℃/W

Electrical Characteristics (T_C=25°C unless otherwise noted)

Symbol	Parameter	Condition	Min	Typ	Max	Unit
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V I_D=-250μA	-60	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current(T_A=25℃)	V_{DS}=-60V, V_{GS}=0V	--	--	-1	μA
	Zero Gate Voltage Drain Current(T_A=125℃)	V_{DS}=-60V, V_{GS}=0V	--	--	-100	uA
I_{GSS}	Gate-Body Leakage Current	V_{GS}=±20V, V_{DS}=0V	--	--	±100	nA
$V_{GS(TH)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=-250μA	-1.0	-1.5	-2.5	V
$R_{DS(ON)}$	Drain-Source On-State Resistance②	V_{GS}=-10V, I_D=-2A	--	160	200	mΩ
$R_{DS(ON)}$	Drain-Source On-State Resistance②	V_{GS}=-4.5V, I_D=-1A	--	200	300	mΩ
C_{iss}	Input Capacitance	V_{DS}=-30V, V_{GS}=0V, f=1MHz	--	310	--	pF
C_{oss}	Output Capacitance		--	22	--	pF
C_{rss}	Reverse Transfer Capacitance		--	15	--	pF
Q_g	Total Gate Charge	V_{DS}=-30V I_D=-2A, V_{GS}=-10V	--	5.4	--	nC
Q_{gs}	Gate Source Charge		--	1.1	--	nC
Q_{gd}	Gate Drain Charge		--	1.6	--	nC
$t_{d(on)}$	Turn on Delay Time	V_{DD}=-30V, I_D=-2A, R_G=3.3Ω, V_{GS}=-10V	--	41	--	ns
t_r	Turn on Rise Time		--	22	--	ns
$t_{d(off)}$	Turn Off Delay Time		-	25	--	ns
t_f	Turn Off Fall Time		--	32	--	ns
I_{SD}	Source drain current(Body Diode)	T_A=25℃	--	--	-2.0	A
V_{SD}	Forward on voltage②	T_j=25℃, I_{SD}=-2A, V_{GS}=0V	--	-0.84	-1.2	V

Notes:

① Pulse width limited by maximum allowable junction temperature

②Pulse test ; Pulse width≤300μs, duty cycle≤2%.

Typical Electrical and Thermal Characteristics (Curves)

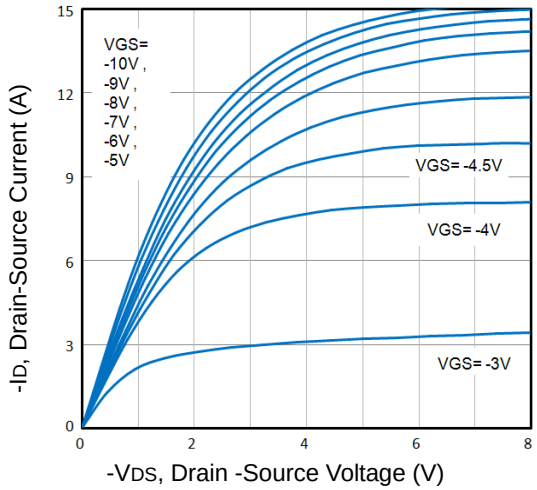


Fig1. Typical Output Characteristics

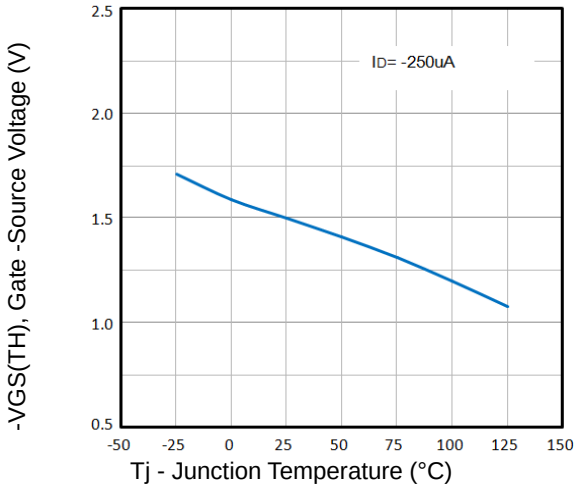


Fig2. Normalized Threshold Voltage Vs. Temperature

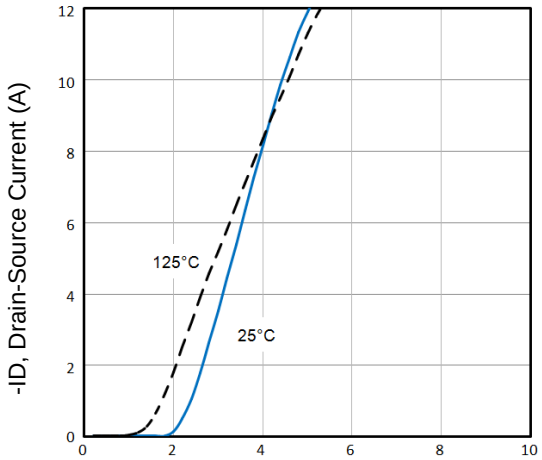


Fig3. Typical Transfer Characteristics

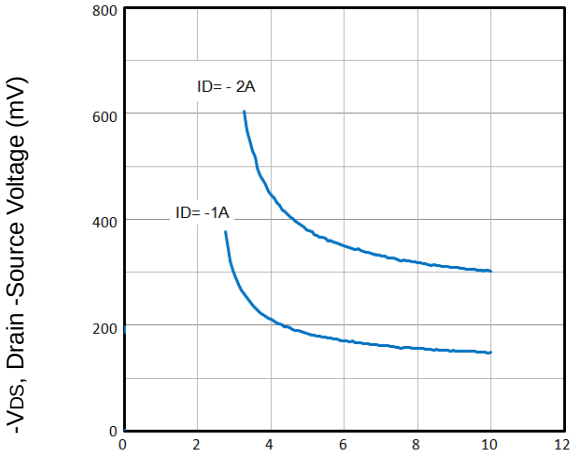


Fig4. Drain -Source Voltage vs Gate -Source Voltage

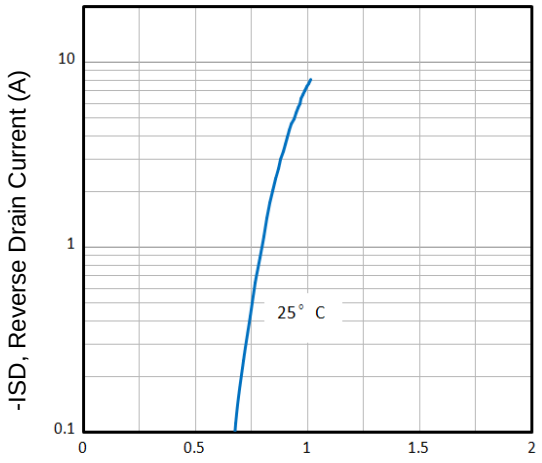


Fig5. Typical Source-Drain Diode Forward Voltage

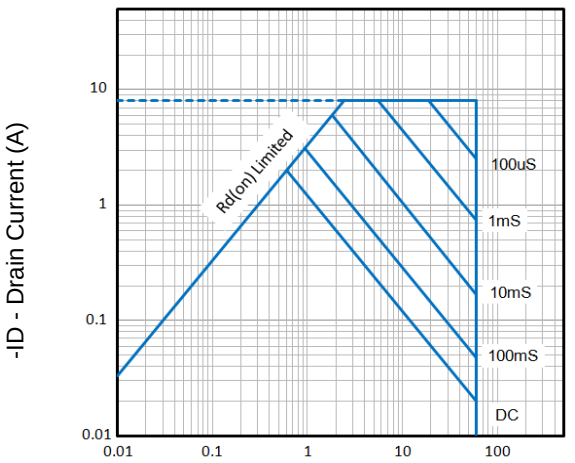


Fig6. Maximum Safe Operating Area

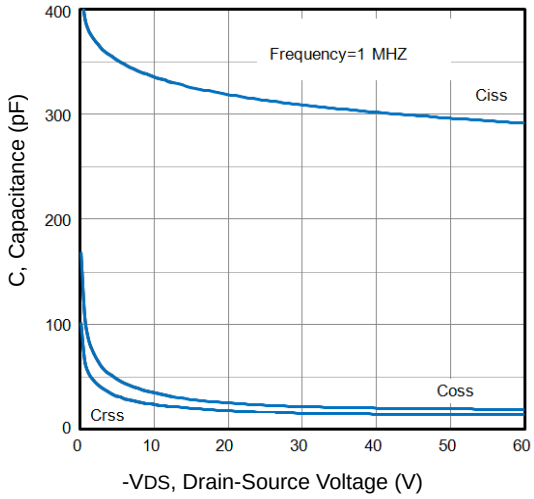


Fig7. Typical Capacitance Vs. Drain-Source Voltage

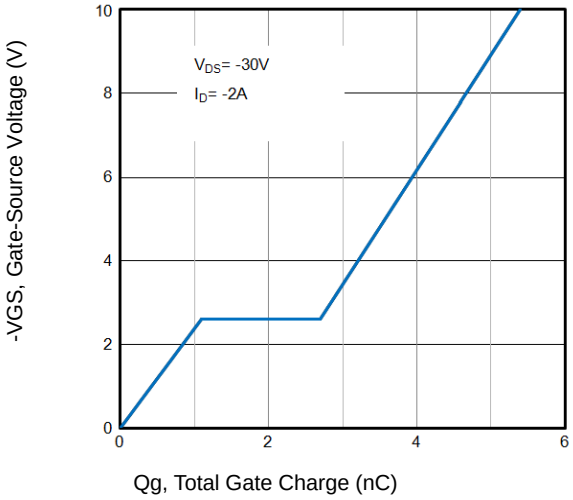


Fig8. Typical Gate Charge Vs. Gate-Source Voltage

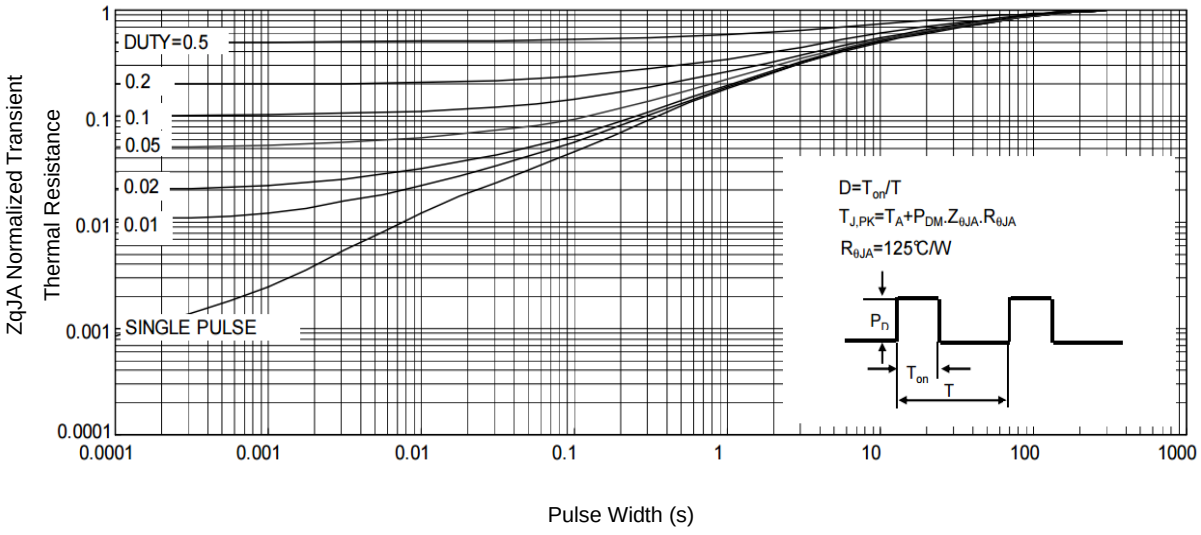


Fig9. Normalized Maximum Transient Thermal Impedance

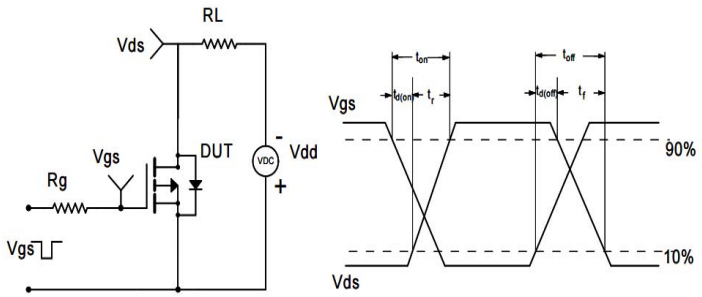
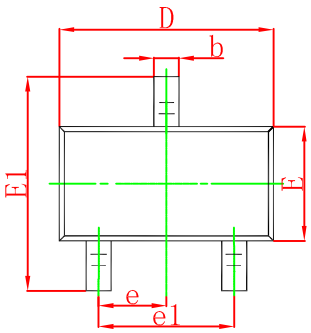
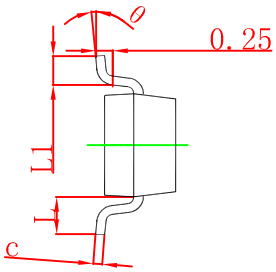
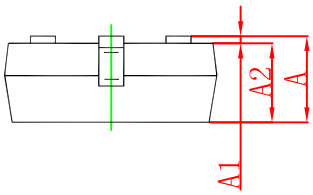


Fig10. Switching Time Test Circuit and waveforms

SOT-23 Package Outline Dimensions

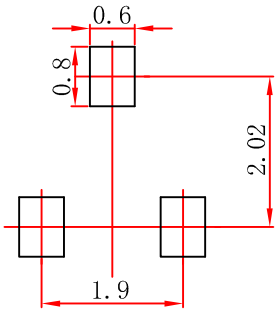






Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

SOT-23 Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:± 0.05mm.
3.The pad layout is for reference purposes only.

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